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Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	EBI/EMI, I ² C, IrDA, SmartCard, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, I ² S, POR, PWM, WDT
Number of I/O	93
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	120-VFBGA
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32wg395f128-bga120

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1 Ordering Information

Table 1.1 (p. 2) shows the available EFM32WG395 devices.

Table 1.1. Ordering Information

Ordering Code	Flash (kB)	RAM (kB)	Max Speed (MHz)	Supply Voltage (V)	Temperature (⁰C)	Package
EFM32WG395F64-BGA120	64	32	48	1.98 - 3.8	-40 - 85	BGA120
EFM32WG395F128-BGA120	128	32	48	1.98 - 3.8	-40 - 85	BGA120
EFM32WG395F256-BGA120	256	32	48	1.98 - 3.8	-40 - 85	BGA120

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to interface the external devices. The timing is adjustable to meet specifications of the external devices. The interface is limited to asynchronous devices.

2.1.11 TFT Direct Drive

The EBI contains a TFT controller which can drive a TFT via a 565 RGB interface. The TFT controller supports programmable display and port sizes and offers accurate control of frequency and setup and hold timing. Direct Drive is supported for TFT displays which do not have their own frame buffer. In that case TFT Direct Drive can transfer data from either on-chip memory or from an external memory device to the TFT at low CPU load. Automatic alpha-blending and masking is also supported for transfers through the EBI interface.

2.1.12 Universal Serial Bus Controller (USB)

The USB is a full-speed USB 2.0 compliant OTG host/device controller. The USB can be used in Device, On-the-go (OTG) Dual Role Device or Host-only configuration. In OTG mode the USB supports both Host Negotiation Protocol (HNP) and Session Request Protocol (SRP). The device supports both full-speed (12MBit/s) and low speed (1.5MBit/s) operation. The USB device includes an internal dedicated Descriptor-Based Scatter/Garther DMA and supports up to 6 OUT endpoints and 6 IN endpoints, in addition to endpoint 0. The on-chip PHY includes all OTG features, except for the voltage booster for supplying 5V to VBUS when operating as host.

2.1.13 Inter-Integrated Circuit Interface (I2C)

The I^2C module provides an interface between the MCU and a serial I^2C -bus. It is capable of acting as both a master and a slave, and supports multi-master buses. Both standard-mode, fast-mode and fast-mode plus speeds are supported, allowing transmission rates all the way from 10 kbit/s up to 1 Mbit/s. Slave arbitration and timeouts are also provided to allow implementation of an SMBus compliant system. The interface provided to software by the I^2C module, allows both fine-grained control of the transmission process and close to automatic transfers. Automatic recognition of slave addresses is provided in all energy modes.

2.1.14 Universal Synchronous/Asynchronous Receiver/Transmitter (US-ART)

The Universal Synchronous Asynchronous serial Receiver and Transmitter (USART) is a very flexible serial I/O module. It supports full duplex asynchronous UART communication as well as RS-485, SPI, MicroWire and 3-wire. It can also interface with ISO7816 SmartCards, IrDA and I2S devices.

2.1.15 Pre-Programmed USB/UART Bootloader

The bootloader presented in application note AN0042 is pre-programmed in the device at factory. The bootloader enables users to program the EFM32 through a UART or a USB CDC class virtual UART without the need for a debugger. The autobaud feature, interface and commands are described further in the application note.

2.1.16 Universal Asynchronous Receiver/Transmitter (UART)

The Universal Asynchronous serial Receiver and Transmitter (UART) is a very flexible serial I/O module. It supports full- and half-duplex asynchronous UART communication.

2.1.17 Low Energy Universal Asynchronous Receiver/Transmitter (LEUART)

The unique LEUARTTM, the Low Energy UART, is a UART that allows two-way UART communication on a strict power budget. Only a 32.768 kHz clock is needed to allow UART communication up to 9600 baud/

s. The LEUART includes all necessary hardware support to make asynchronous serial communication possible with minimum of software intervention and energy consumption.

2.1.18 Timer/Counter (TIMER)

The 16-bit general purpose Timer has 3 compare/capture channels for input capture and compare/Pulse-Width Modulation (PWM) output. TIMER0 also includes a Dead-Time Insertion module suitable for motor control applications.

2.1.19 Real Time Counter (RTC)

The Real Time Counter (RTC) contains a 24-bit counter and is clocked either by a 32.768 kHz crystal oscillator, or a 32.768 kHz RC oscillator. In addition to energy modes EM0 and EM1, the RTC is also available in EM2. This makes it ideal for keeping track of time since the RTC is enabled in EM2 where most of the device is powered down.

2.1.20 Backup Real Time Counter (BURTC)

The Backup Real Time Counter (BURTC) contains a 32-bit counter and is clocked either by a 32.768 kHz crystal oscillator, a 32.768 kHz RC oscillator or a 1 kHz ULFRCO. The BURTC is available in all Energy Modes and it can also run in backup mode, making it operational even if the main power should drain out.

2.1.21 Low Energy Timer (LETIMER)

The unique LETIMERTM, the Low Energy Timer, is a 16-bit timer that is available in energy mode EM2 in addition to EM1 and EM0. Because of this, it can be used for timing and output generation when most of the device is powered down, allowing simple tasks to be performed while the power consumption of the system is kept at an absolute minimum. The LETIMER can be used to output a variety of waveforms with minimal software intervention. It is also connected to the Real Time Counter (RTC), and can be configured to start counting on compare matches from the RTC.

2.1.22 Pulse Counter (PCNT)

The Pulse Counter (PCNT) can be used for counting pulses on a single input or to decode quadrature encoded inputs. It runs off either the internal LFACLK or the PCNTn_S0IN pin as external clock source. The module may operate in energy mode EM0 – EM3.

2.1.23 Analog Comparator (ACMP)

The Analog Comparator is used to compare the voltage of two analog inputs, with a digital output indicating which input voltage is higher. Inputs can either be one of the selectable internal references or from external pins. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.24 Voltage Comparator (VCMP)

The Voltage Supply Comparator is used to monitor the supply voltage from software. An interrupt can be generated when the supply falls below or rises above a programmable threshold. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.25 Analog to Digital Converter (ADC)

The ADC is a Successive Approximation Register (SAR) architecture, with a resolution of up to 12 bits at up to one million samples per second. The integrated input mux can select inputs from 8 external pins and 6 internal signals.



Module	Configuration	Pin Connections
VCMP	Full configuration	NA
ADC0	Full configuration	ADC0_CH[7:0]
DAC0	Full configuration	DAC0_OUT[1:0], DAC0_OUTxALT
ОРАМР	Full configuration	Outputs: OPAMP_OUTx, OPAMP_OUTxALT, Inputs: OPAMP_Px, OPAMP_Nx
AES	Full configuration	NA
GPIO	93 pins	Available pins are shown in Table 4.3 (p. 68)

2.3 Memory Map

The *EFM32WG395* memory map is shown in Figure 2.2 (p. 9), with RAM and Flash sizes for the largest memory configuration.

Figure 2.2. EFM32WG395 Memory Map with largest RAM and Flash sizes





Symbol	Parameter	Condition	Min	Тур	Max	Unit
		1.2 MHz HFRCO, all peripher- al clocks disabled, V_{DD} = 3.0 V, T_{AMB} =25°C		271	286	µA/ MHz
		1.2 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V, T_{AMB} =85°C		275		μΑ/ MHz
	EM1 current (Pro- duction test condi- tion = 14 MHz)	48 MHz HFXO, all peripheral clocks disabled, V_{DD} = 3.0 V, T_{AMB} =25°C		63	75	µA/ MHz
		48 MHz HFXO, all peripheral clocks disabled, V_{DD} = 3.0 V, T_{AMB} =85°C		65	76	µA/ MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V, T_{AMB} =25°C		64	75	µA/ MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V, T_{AMB} =85°C		65	77	μΑ/ MHz
		21 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V, T_{AMB} =25°C		65	76	μΑ/ MHz
		21 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V, T_{AMB} =85°C		66	78	μΑ/ MHz
leu.	EM1 current (Pro-	14 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V, T_{AMB} =25°C		67	79	µA/ MHz
	tion = 14 MHz)	14 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V, T_{AMB} =85°C		68	82	μΑ/ MHz
		11 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V, T_{AMB} =25°C		68	81	μΑ/ MHz
		11 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V, T_{AMB} =85°C		70	83	μΑ/ MHz
		6.6 MHz HFRCO, all peripher- al clocks disabled, V_{DD} = 3.0 V, T_{AMB} =25°C		74	87	μΑ/ MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V, T_{AMB} =85°C		76	89	µA/ MHz
		1.2 MHz HFRCO. all peripheral clocks disabled, V_{DD} = 3.0 V, T_{AMB} =25°C		106	120	μΑ/ MHz
		1.2 MHz HFRCO. all peripheral clocks disabled, V_{DD} = 3.0 V, T_{AMB} =85°C		112	129	μΑ/ MHz
I _{EM2}	EM2 current	EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V_{DD} = 3.0 V, T_{AMB} =25°C		0.95 ¹	1.7 ¹	μΑ



Symbol	Parameter	Condition	Min	Тур	Мах	Unit
		EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V_{DD} = 3.0 V, T_{AMB} =85°C		3.0 ¹	4.0 ¹	μA
1	EM2 current	V _{DD} = 3.0 V, T _{AMB} =25°C		0.65	1.3	μA
I 'EM3	EWIS current	V _{DD} = 3.0 V, T _{AMB} =85°C		2.65	4.0	μA
	EM4 current	V _{DD} = 3.0 V, T _{AMB} =25°C		0.02	0.055	μA
I EM4		V _{DD} = 3.0 V, T _{AMB} =85°C		0.44	0.9	μA

¹Using backup RTC.

3.4.1 EM1 Current Consumption

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Figure 3.1. EM1 Current consumption with all peripheral clocks disabled and HFXO running at 48MHz
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Figure 3.2. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 28MHz









3.4.2 EM2 Current Consumption

Figure 3.8. EM2 current consumption. RTC¹ prescaled to 1kHz, 32.768 kHz LFRCO.



¹Using backup RTC.

3.7 Flash

Table 3.7. Flash

Symbol	Parameter	Condition	Min	Тур	Max	Unit
EC _{FLASH}	Flash erase cycles before failure		20000			cycles
		T _{AMB} <150°C	10000			h
RET _{FLASH}	Flash data retention	T _{AMB} <85°C	10			years
		T _{AMB} <70°C	20			years
t _{W_PROG}	Word (32-bit) pro- gramming time		20			μs
t _{PERASE}	Page erase time		20	20.4	20.8	ms
t _{DERASE}	Device erase time		40	40.8	41.6	ms
I _{ERASE}	Erase current				7 ¹	mA
I _{WRITE}	Write current				7 ¹	mA
V _{FLASH}	Supply voltage dur- ing flash erase and write		1.98		3.8	V

¹Measured at 25°C

3.8 General Purpose Input Output

Table 3.8. GPIO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
V _{IOIL}	Input low voltage				0.30V _{DD}	V
V _{IOIH}	Input high voltage		0.70V _{DD}			V
		Sourcing 0.1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.80V _{DD}		V
V _{ЮОН}	Output high volt- age (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sourcing 0.1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.90V _{DD}		V
		Sourcing 1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.85V _{DD}		V
		Sourcing 1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.90V _{DD}		V
		Sourcing 6 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.75V _{DD}			V
		Sourcing 6 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.85V _{DD}			V
		Sourcing 20 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.60V _{DD}			V



Figure 3.14. Typical High-Level Output Current, 3V Supply Voltage



GPIO_Px_CTRL DRIVEMODE = STANDARD





Figure 3.16. Typical High-Level Output Current, 3.8V Supply Voltage



GPIO_Px_CTRL DRIVEMODE = STANDARD

GPIO_Px_CTRL DRIVEMODE = HIGH



Symbol	Parameter	Condition	Min	Тур	Max	Unit
		200 kSamples/s, 12 bit, differ- ential, internal 1.25V reference		79		dBc
		200 kSamples/s, 12 bit, differ- ential, internal 2.5V reference		79		dBc
		200 kSamples/s, 12 bit, differ- ential, 5V reference		78		dBc
		200 kSamples/s, 12 bit, differential, V_{DD} reference	68	79		dBc
		200 kSamples/s, 12 bit, differ- ential, 2xV _{DD} reference		79		dBc
	Offect voltage	After calibration, single ended	-3.5	0.3	3	mV
V ADCOFFSET	Unset Voltage	After calibration, differential		0.3		mV
				-1.92		mV/°C
TGRAD _{ADCTH}	Thermometer out- put gradient			-6.3		ADC Codes/ °C
DNL _{ADC}	Differential non-lin- earity (DNL)		-1	±0.7	4	LSB
INL _{ADC}	Integral non-linear- ity (INL), End point method			±1.2	±3	LSB
MC _{ADC}	No missing codes		11.999 ¹	12		bits
CAIN	Coip orror drift	1.25V reference		0.01 ²	0.033 ³	%/°C
GAINED		2.5V reference		0.01 ²	0.03 ³	%/°C
OFFRET	Offect error drift	1.25V reference		0.2 ²	0.7 ³	LSB/°C
DNL _{ADC} INL _{ADC} MC _{ADC} GAIN _{ED} OFFSET _{ED}		2.5V reference		0.2 ²	0.62 ³	LSB/°C

¹On the average every ADC will have one missing code, most likely to appear around 2048 +/- n*512 where n can be a value in the set {-3, -2, -1, 1, 2, 3}. There will be no missing code around 2048, and in spite of the missing code the ADC will be monotonic at all times so that a response to a slowly increasing input will always be a slowly increasing output. Around the one code that is missing, the neighbour codes will look wider in the DNL plot. The spectra will show spurs on the level of -78dBc for a full scale input for chips that have the missing code issue.

²Typical numbers given by abs(Mean) / (85 - 25).

³Max number given by (abs(Mean) + 3x stddev) / (85 - 25).

The integral non-linearity (INL) and differential non-linearity parameters are explained in Figure 3.24 (p. 37) and Figure 3.25 (p. 37), respectively.



Figure 3.24. Integral Non-Linearity (INL)



Figure 3.25. Differential Non-Linearity (DNL)



Figure 3.28. ADC Differential Linearity Error vs Code, Vdd = 3V, Temp = 25°C





Symbol	Parameter	Condition	Min	Тур	Max	Unit
		500 kSamples/s, 12 bit, differ- ential, internal 2.5V reference		58		dB
		500 kSamples/s, 12 bit, differential, V_{DD} reference		59		dB
		500 kSamples/s, 12 bit, sin- gle ended, internal 1.25V refer- ence		57		dB
	Signal to Noise-	500 kSamples/s, 12 bit, single ended, internal 2.5V reference		54		dB
SNDR _{DAC}	pulse Distortion Ra- tio (SNDR)	500 kSamples/s, 12 bit, differ- ential, internal 1.25V reference		56		dB
		500 kSamples/s, 12 bit, differ- ential, internal 2.5V reference		53		dB
	500 kSamples/s, 12 bit, differential, V_{DD} reference		55		dB	
	Spurious Free	500 kSamples/s, 12 bit, sin- gle ended, internal 1.25V refer- ence		62		dBc
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		56		dBc
SFDR _{DAC}	Dynamic Range(SFDR)	500 kSamples/s, 12 bit, differ- ential, internal 1.25V reference		61		dBc
		500 kSamples/s, 12 bit, differ- ential, internal 2.5V reference		55		dBc
		500 kSamples/s, 12 bit, differential, V_{DD} reference		60		dBc
V=	Offset voltage	After calibration, single ended		2	9	mV
V DACOFFSET	Onset voltage	After calibration, differential		2		mV
DNL _{DAC}	Differential non-lin- earity			±1		LSB
INL _{DAC}	Integral non-lineari- ty			±5		LSB
MC _{DAC}	No missing codes			12		bits

¹Measured with a static input code and no loading on the output.

3.12 Operational Amplifier (OPAMP)

The electrical characteristics for the Operational Amplifiers are based on simulations.

Table 3.17. OPAMP

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
		(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0, Unity Gain		370	460	μA
	Active Current	(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1, Unity Gain		95	135	μA



Symbol	Parameter	Condition	Min	Тур	Max	Unit
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1, Unity Gain		13	25	μA
		(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		101		dB
G _{OL}	Open Loop Gain	(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		98		dB
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		91		dB
		(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		6.1		MHz
GBW _{OPAMP}	Gain Bandwidth Product	(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		1.8		MHz
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		0.25		MHz
		(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0, CL=75 pF		64		0
PM _{OPAMP}	Phase Margin	(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1, C _L =75 pF		58		o
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1, C _L =75 pF		58		0
R _{INPUT}	Input Resistance			100		Mohm
R _{LOAD}	Load Resistance		200			Ohm
I _{LOAD_DC}	DC Load Current				11	mA
Vinduz	Input Voltage	OPAxHCMDIS=0	V _{SS}		V_{DD}	V
VINPU1	input voltage	OPAxHCMDIS=1	V _{SS}		V _{DD} -1.2	V
V _{OUTPUT}	Output Voltage		V _{SS}		V_{DD}	V
Vereer	Input Offset Voltage	Unity Gain, V _{SS} <v<sub>in<v<sub>DD, OPAxHCMDIS=0</v<sub></v<sub>	-13	0	11	mV
VOFFSET	input Onset Voltage	Unity Gain, V _{SS} <v<sub>in<_{DD}-1.2, OPAxHCMDIS=1</v<sub>		1		mV
V _{OFFSET_DRIFT}	Input Offset Voltage Drift				0.02	mV/°C
		(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		3.2		V/µs
SR _{OPAMP}	Slew Rate	(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		0.8		V/µs
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		0.1		V/µs
N	Voltage Notice	V _{out} =1V, RESSEL=0, 0.1 Hz <f<10 khz,="" opax-<br="">HCMDIS=0</f<10>		101		μV _{RMS}
NOPAMP	voitage Noise	V _{out} =1V, RESSEL=0, 0.1 Hz <f<10 khz,="" opax-<br="">HCMDIS=1</f<10>		141		μV _{RMS}



Figure 3.34. OPAMP Negative Power Supply Rejection Ratio



Figure 3.35. OPAMP Voltage Noise Spectral Density (Unity Gain) Vout=1V



Figure 3.36. OPAMP Voltage Noise Spectral Density (Non-Unity Gain)





Symbol	Parameter	Min	Тур	Мах	Unit
t _{H_ARDY} ¹²³⁴	Hold time, from trailing EBI_REn, EBI_WEn edge to EBI_ARDY invalid	-1 + (3 * t _{HFCORECLK})			ns

¹Applies for all addressing modes (figure only shows D16A8.)

²Applies for EBI_REn, EBI_WEn (figure only shows EBI_REn)

³Applies for all polarities (figure only shows active low signals)

 $^4\text{Measurement}$ done at 10% and 90% of V_{DD} (figure shows 50% of $_{\text{VDD}})$

3.16 I2C

Table 3.25. I2C Standard-mode (Sm)

Symbol	Parameter	Min	Тур	Max	Unit
f _{SCL}	SCL clock frequency	0		100 ¹	kHz
t _{LOW}	SCL clock low time	4.7			μs
t _{HIGH}	SCL clock high time	4.0			μs
t _{SU,DAT}	SDA set-up time	250			ns
t _{HD,DAT}	SDA hold time	8		3450 ^{2,3}	ns
t _{SU,STA}	Repeated START condition set-up time	4.7			μs
t _{HD,STA}	(Repeated) START condition hold time	4.0			μs
t _{SU,STO}	STOP condition set-up time	4.0			μs
t _{BUF}	Bus free time between a STOP and a START condition	4.7			μs

¹For the minimum HFPERCLK frequency required in Standard-mode, see the I2C chapter in the EFM32WG Reference Manual. ²The maximum SDA hold time ($t_{HD,DAT}$) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}). ³When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < ((3450*10⁻⁹ [s] * f_{HFPERCLK} [Hz]) - 4).

Table 3.26. I2C Fast-mode (Fm)

Symbol	Parameter	Min	Тур	Мах	Unit
f _{SCL}	SCL clock frequency	0		400 ¹	kHz
t _{LOW}	SCL clock low time	1.3			μs
t _{HIGH}	SCL clock high time	0.6			μs
t _{SU,DAT}	SDA set-up time	100			ns
t _{HD,DAT}	SDA hold time	8		900 ^{2,3}	ns
t _{SU,STA}	Repeated START condition set-up time	0.6			μs
t _{HD,STA}	(Repeated) START condition hold time	0.6			μs
t _{SU,STO}	STOP condition set-up time	0.6			μs
t _{BUF}	Bus free time between a STOP and a START condition	1.3			μs

¹For the minimum HFPERCLK frequency required in Fast-mode, see the I2C chapter in the EFM32WG Reference Manual.

²The maximum SDA hold time ($t_{HD,DAT}$) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}). ³When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < ((900*10⁻⁹ [s] * $f_{HEPERCLK}$ [Hz]) - 4).



В	GA120 Pin# and Name	Pin Alternate Functionality / Description						
Pin #	Pin Name	Analog	EBI	Timers	Communication	Other		
H11	VDD_DREG	Power supply for on-chip voltage regulator.						
H12	PE2	BU_VOUT	EBI_A09 #0	TIM3_CC2 #1	U1_TX #3	ACMP0_O #1		
H13	PC7	ACMP0_CH7	EBI_A06 #0/1/2		LEU1_RX #0 I2C0_SCL #2	LES_CH7 #0 ETM_TD0 #2		
J1	PD14				I2C0_SDA #3			
J2	PD15				I2C0_SCL #3			
J3	VSS	Ground						
J11	IOVDD_3	Digital IO power supply 3.						
J12	PC6	ACMP0_CH6	EBI_A05 #0/1/2		LEU1_TX #0 I2C0_SDA #2	LES_CH6 #0 ETM_TCLK #2		
J13	DECOUPLE	Decouple output for on-o	chip voltage regulator. An ex	kternal capacitance of size	e C _{DECOUPLE} is required at th	nis pin.		
К1	PC0	ACMP0_CH0 DAC0_OUT0ALT #0/ OPAMP_OUT0ALT	EBI_A23 #0/1/2	TIM0_CC1 #4 PCNT0_S0IN #2	US0_TX #5 US1_TX #0 I2C0_SDA #4	LES_CH0 #0 PRS_CH2 #0		
К2	PC1	ACMP0_CH1 DAC0_OUT0ALT #1/ OPAMP_OUT0ALT	EBI_A24 #0/1/2	TIM0_CC2 #4 PCNT0_S1IN #2	US0_RX #5 US1_RX #0 I2C0_SCL #4	LES_CH1 #0 PRS_CH3 #0		
К3	IOVDD_4	Digital IO power supply	4.	I				
K11	VSS	Ground						
K12	VSS	Ground						
K13	PD8	BU_VIN				CMU_CLK1 #1		
L1	PC2	ACMP0_CH2 DAC0_OUT0ALT #2/ OPAMP_OUT0ALT	EBI_A25 #0/1/2	TIM0_CDTI0 #4	US2_TX #0	LES_CH2 #0		
L2	PC3	ACMP0_CH3 DAC0_OUT0ALT #3/ OPAMP_OUT0ALT	EBI_NANDREn #0/1/2	TIM0_CDTI1 #4	US2_RX #0	LES_CH3 #0		
L3	PA7		EBI_CSTFT #0/1/2					
L4	IOVDD_5	Digital IO power supply 5.						
L5	VSS	Ground						
L6	VSS	Ground						
L7	IOVDD_6	5 Digital IO power supply 6.						
L8	PB9		EBI_A03 #0/1/2		U1_TX #2			
L9	PB10		EBI_A04 #0/1/2		U1_RX #2			
L10	PD0	ADC0_CH0 DAC0_OUT0ALT #4/ OPAMP_OUT0ALT OPAMP_OUT2 #1		PCNT2_S0IN #0	US1_TX #1			
L11	PD1	ADC0_CH1 DAC0_OUT1ALT #4/ OPAMP_OUT1ALT		TIM0_CC0 #3 PCNT2_S1IN #0	US1_RX #1	DBG_SWO #2		
L12	PD4	ADC0_CH4 OPAMP_P2			LEU0_TX #0	ETM_TD2 #0/2		
L13	PD7	ADC0_CH7 DAC0_N1 / OPAMP_N1		TIM1_CC1 #4 LETIM0_OUT1 #0 PCNT0_S1IN #3	US1_TX #2 I2C0_SCL #1	CMU_CLK0 #2 LES_ALTEX1 #0 ACMP1_O #2 ETM_TCLK #0		
M1	PB7	LFXTAL_P		TIM1_CC0 #3	US0_TX #4 US1_CLK #0			

6 Chip Marking, Revision and Errata

6.1 Chip Marking

In the illustration below package fields and position are shown.

Figure 6.1. Example Chip Marking (top view)



6.2 Revision

The revision of a chip can be determined from the "Revision" field in Figure 6.1 (p. 73).

6.3 Errata

Please see the errata document for EFM32WG395 for description and resolution of device erratas. This document is available in Simplicity Studio and online at: http://www.silabs.com/support/pages/document-library.aspx?p=MCUs--32-bit

B Contact Information

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Please visit the Silicon Labs Technical Support web page: http://www.silabs.com/support/pages/contacttechnicalsupport.aspx and register to submit a technical support request.